

Dedicated to the memory of Prof. M. Sheinkman effect of ultrasonic treatment on the defect structure of the Si-SiO₂ system

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Effect of ultrasonic treatment on the defect structure of the Si-SiO₂ system

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Interaktsioon punktdefektide ja lisandite vahel süsteemis Si-SiO₂ ja nende mõju piirpinna omadustele : [ettekande sisukokkuvõte]

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